

Electronic Supplementary Information

Improved Nitrogen Reduction Activity of NbSe₂ Tuned by Edge Chirality

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Table S1 H adsorption energy on NbSe₂ edges.

NbSe ₂ edge model	H adsorption energy (eV)
Zigzag	-0.16
Zigzag with one Se vacancy	-1.79
Armchair	0.28
Armchair with one Se vacancy	0.29

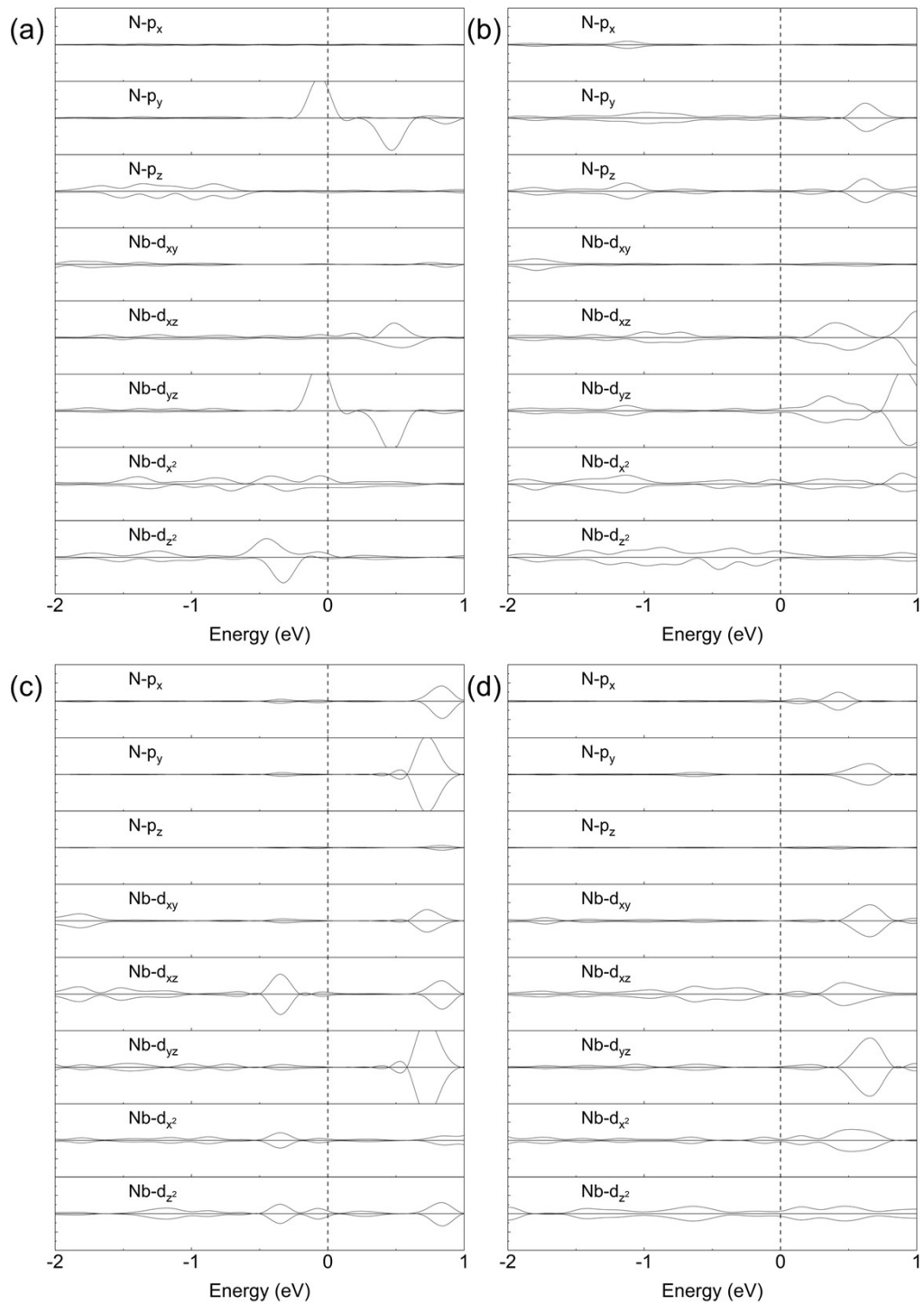


Figure S1. Density of states projected on (PDOS) N 2p states and Nb 4d states on (a) zigzag edge and (b) zigzag edge with one Se vacancy via side-on pattern, (c) armchair edge and (d) armchair edge of NbSe₂ via end-on pattern, respectively.

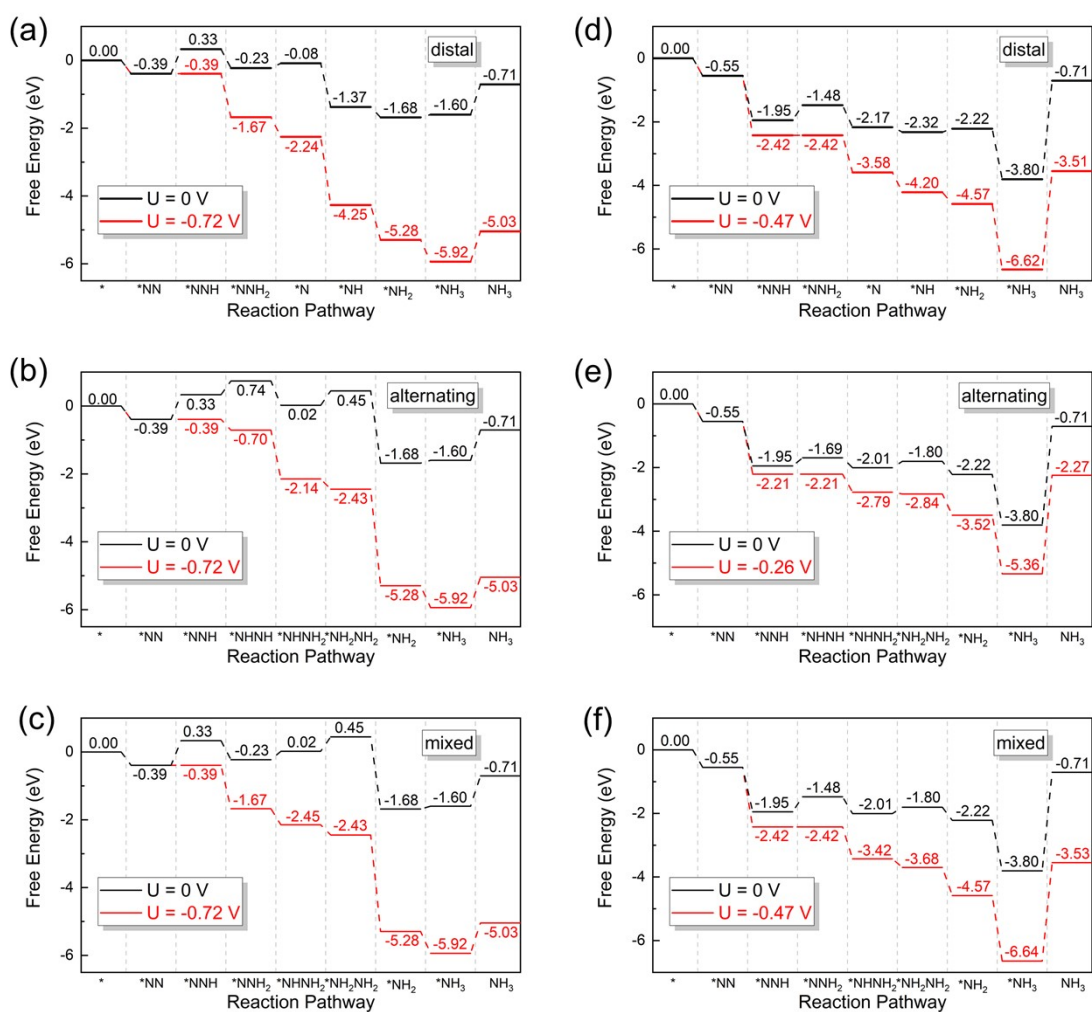


Figure S2. Gibbs free energy diagrams of distal, alternating and mixed pathway on pristine zigzag edge (a) (b) (c), zigzag edge with a Se vacancy (d) (e) (f).

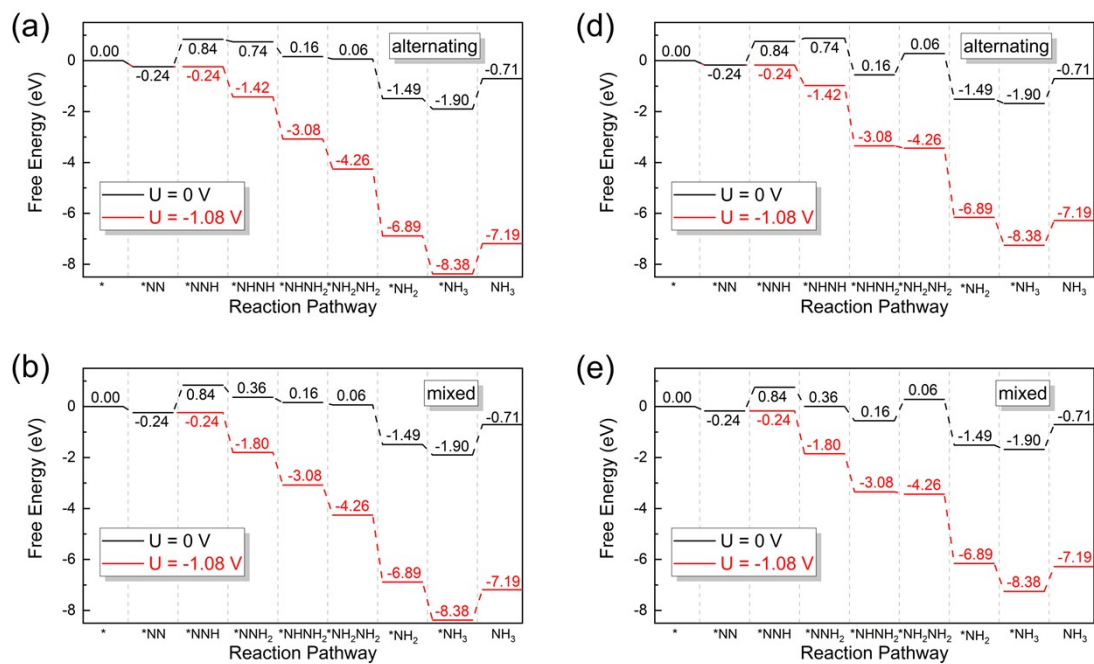


Figure S3. Gibbs free energy diagrams of alternating and mixed pathway on pristine armchair edge (a) (b), armchair edge with a Se vacancy (c) (d).